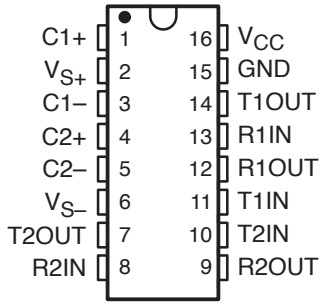
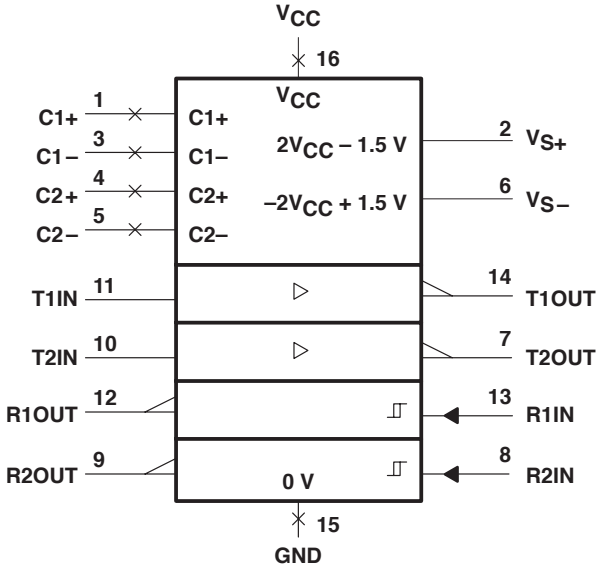
- **Operates With Single 5-V Power Supply**
- **LinBiCMOS™ Process Technology**
- **Two Drivers and Two Receivers**
- **±30-V Input Levels**
- **Low Supply Current . . . 8 mA Typical**
- **Meets or Exceeds TIA/EIA-232-F and ITU Recommendation V.28**
- **Designed to be Interchangeable With Maxim MAX232**
- **Applications**
  - **TIA/EIA-232-F**
  - **Battery-Powered Systems**
  - **Terminals**
  - **Modems**
  - **Computers**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015**
- **Package Options Include Plastic Small-Outline (D, DW) Packages and Standard Plastic (N) DIPs**

D, DW, OR N PACKAGE
(TOP VIEW)



logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

description

The MAX232 device is a dual driver/receiver that includes a capacitive voltage generator to supply EIA-232 voltage levels from a single 5-V supply. Each receiver converts EIA-232 inputs to 5-V TTL/CMOS levels. These receivers have a typical threshold of 1.3 V and a typical hysteresis of 0.5 V, and can accept ±30-V inputs. Each driver converts TTL/CMOS input levels into EIA-232 levels. The driver, receiver, and voltage-generator functions are available as cells in the Texas Instruments LinASIC™ library.

The MAX232 is characterized for operation from 0°C to 70°C. The MAX232I is characterized for operation from –40°C to 85°C.

AVAILABLE OPTIONS

T_A	PACKAGED DEVICES		
	SMALL OUTLINE (D)	SMALL OUTLINE (DW)	PLASTIC DIP (N)
0°C to 70°C	MAX232D‡	MAX232DW‡	MAX232N
–40°C to 85°C	MAX232ID‡	MAX232IDW‡	MAX232IN

‡ This device is available taped and reeled by adding an R to the part number (i.e., MAX232DR).

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Input supply voltage range, V_{CC} (see Note 1) . . . . . –0.3 V to 6 V
Positive output supply voltage range, V_{S+} . . . . . V_{CC} –0.3 V to 15 V
Negative output supply voltage range, V_{S-} . . . . . –0.3 V to –15 V
Input voltage range, V_I: Driver . . . . . –0.3 V to V_{CC} + 0.3 V
Receiver . . . . . ±30 V
Output voltage range, V_O: T1OUT, T2OUT . . . . . V_{S-} –0.3 V to V_{S+} + 0.3 V
R1OUT, R2OUT . . . . . –0.3 V to V_{CC} + 0.3 V
Short-circuit duration: T1OUT, T2OUT . . . . . Unlimited
Package thermal impedance, θ_{JA} (see Note 2): D package . . . . . 113°C/W
DW package . . . . . 105°C/W
N package . . . . . 78°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . . 260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to network ground terminal.

2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, V_{CC}		4.5	5	5.5	V
High-level input voltage, V_{IH} (T1IN,T2IN)		2			V
Low-level input voltage, V_{IL} (T1IN, T2IN)				0.8	V
Receiver input voltage, R1IN, R2IN				±30	V
Operating free-air temperature, T_A	MAX232	0		70	°C
	MAX232I	–40		85	

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature range (unless otherwise noted)

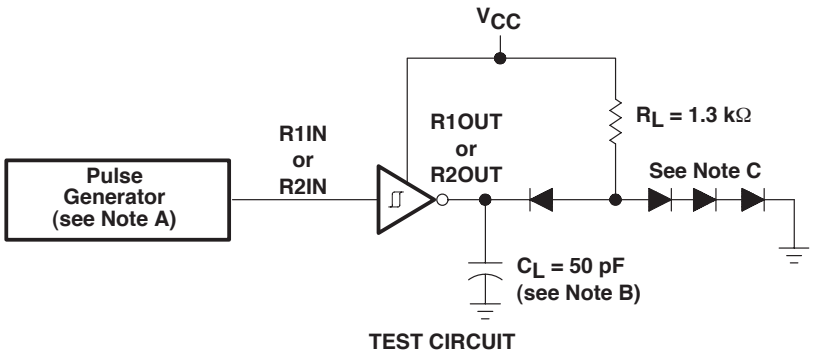
PARAMETER			TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	T1OUT, T2OUT	R_L = 3 kΩ to GND		5	7		V
		R1OUT, R2OUT	I_{OH} = –1 mA		3.5			
V_{OL}	Low-level output voltage‡	T1OUT, T2OUT	R_L = 3 kΩ to GND			–7	–5	V
		R1OUT, R2OUT	I_{OL} = 3.2 mA				0.4	
V_{IT+}	Receiver positive-going input threshold voltage	R1IN, R2IN	V_{CC} = 5 V,	T_A = 25°C		1.7	2.4	V
$V_{IT–}$	Receiver negative-going input threshold voltage	R1IN, R2IN	V_{CC} = 5 V,	T_A = 25°C	0.8	1.2		V
V_{hys}	Input hysteresis voltage	R1IN, R2IN	V_{CC} = 5 V		0.2	0.5	1	V
r_i	Receiver input resistance	R1IN, R2IN	V_{CC} = 5,	T_A = 25°C	3	5	7	kΩ
r_o	Output resistance	T1OUT, T2OUT	$V_{S+} = V_{S–}$ = 0,	V_O = ± 2 V	300			Ω
I_{OS}§	Short-circuit output current	T1OUT, T2OUT	V_{CC} = 5.5 V,	V_O = 0		±10		mA
I_{IS}	Short-circuit input current	T1IN, T2IN	V_I = 0				200	μA
I_{CC}	Supply current		V_{CC} = 5.5 V, T_A = 25°C	All outputs open,		8	10	mA

† All typical values are at V_{CC} = 5 V, T_A = 25°C.
‡ The algebraic convention, in which the least positive (most negative) value is designated minimum, is used in this data sheet for logic voltage levels only.
§ Not more than one output should be shorted at a time.

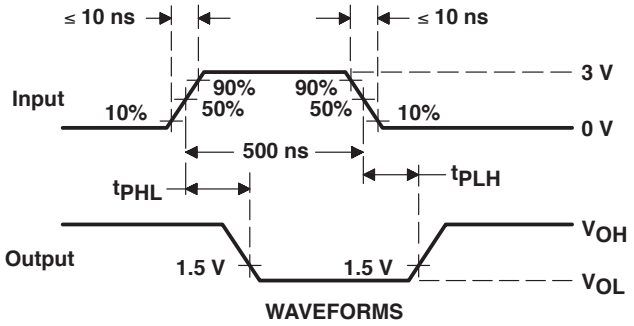
switching characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{PLH(R)}$	Receiver propagation delay time, low- to high-level output	See Figure 1		500		ns
$t_{PHL(R)}$	Receiver propagation delay time, high- to low-level output	See Figure 1		500		ns
SR	Driver slew rate	R_L = 3 kΩ to 7 kΩ, See Figure 2			30	V/μs
SR(tr)	Driver transition region slew rate	See Figure 3		3		V/μs

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

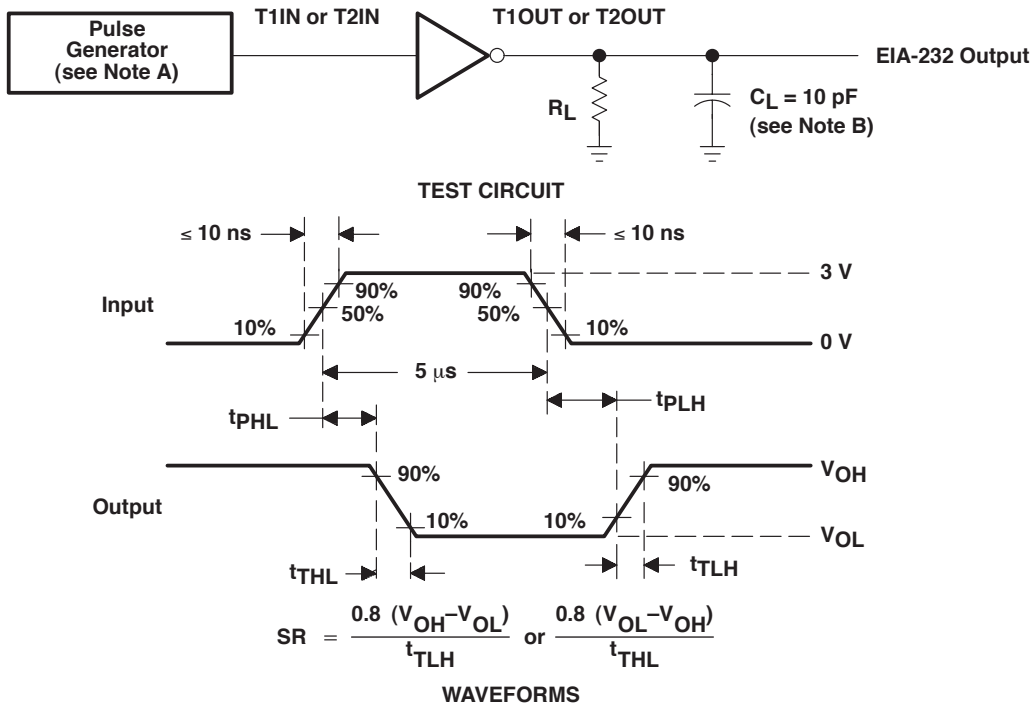


WAVEFORMS

NOTES: A. The pulse generator has the following characteristics: Z_O = 50 Ω, duty cycle ≤ 50%.
B. C_L includes probe and jig capacitance.
C. All diodes are 1N3064 or equivalent.

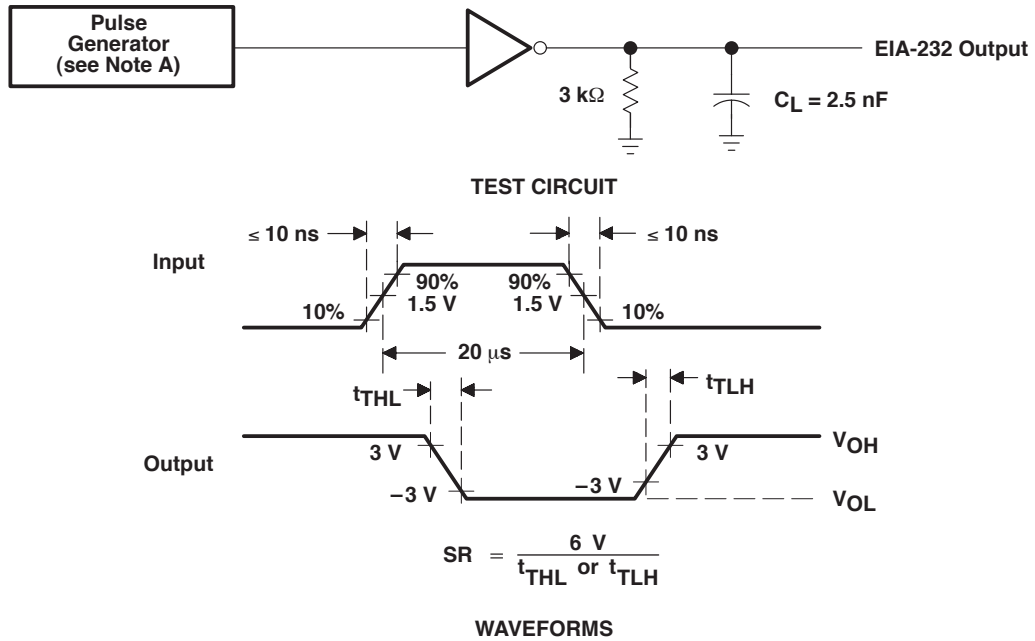
Figure 1. Receiver Test Circuit and Waveforms for t_{PHL} and t_{PLH} Measurements

PARAMETER MEASUREMENT INFORMATION



NOTES: A. The pulse generator has the following characteristics: Z_O = 50 Ω, duty cycle ≤ 50%.
B. C_L includes probe and jig capacitance.

Figure 2. Driver Test Circuit and Waveforms for t_{PHL} and t_{PLH} Measurements (5-μs input)



NOTE A: The pulse generator has the following characteristics: Z_O = 50 Ω, duty cycle ≤ 50%.

Figure 3. Test Circuit and Waveforms for t_{THL} and t_{TLH} Measurements (20-μs input)

APPLICATION INFORMATION

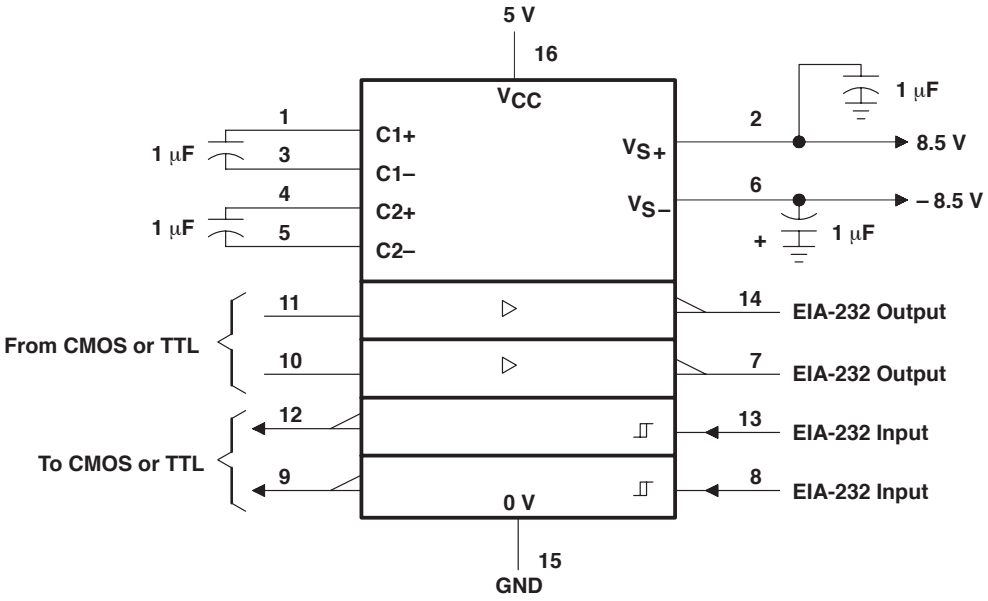


Figure 4. Typical Operating Circuit

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